

TOSHIBA FIELD EFFECT TRANSISTOR SILICON N CHANNEL MOS TYPE (π -MOSII⁵)

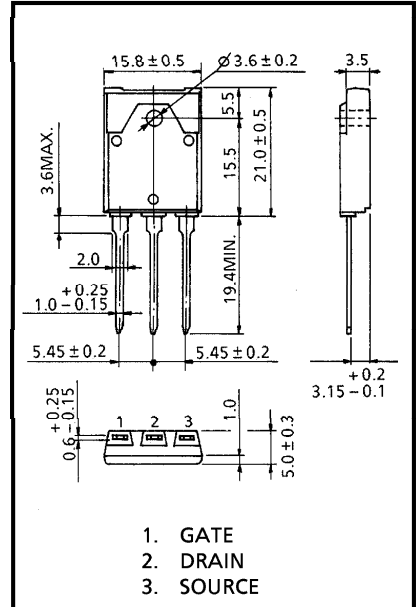
2SK1365

HIGH SPEED, HIGH CURRENT SWITCHING APPLICATIONS
 SWITCHING POWER SUPPLY APPLICATIONS

INDUSTRIAL APPLICATIONS

Unit in mm

- Low Drain-Source ON Resistance : $R_{DS(ON)} = 1.5\Omega$ (Typ.)
- High Forward Transfer Admittance : $|Y_{fs}| = 4.0S$ (Typ.)
- Low Leakage Current : $I_{DSS} = 300\mu A$ (Max.) ($V_{DS} = 800V$)
- Enhancement-Mode : $V_{th} = 1.5 \sim 3.5V$
 ($V_{DS} = 10V, I_D = 1mA$)



JEDEC	—
EIAJ	—
TOSHIBA	2-16F1B

Weight : 5.8g

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Drain-Source Voltage		V_{DSS}	1000	V
Drain-Gate Voltage ($R_{GS} = 20k\Omega$)		V_{DGR}	1000	V
Gate-Source Voltage		V_{GSS}	± 20	V
Drain Current	DC	I_D	7	A
	Pulse	I_{DP}	21	
Drain Power Dissipation ($T_c = 25^\circ C$)		P_D	90	W
Channel Temperature		T_{ch}	150	$^\circ C$
Storage Temperature Range		T_{stg}	$-55 \sim 150$	$^\circ C$

THERMAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	MAX.	UNIT
Thermal Resistance, Channel to Case	$R_{th(ch-c)}$	1.39	$^\circ C / W$
Thermal Resistance, Channel to Ambient	$R_{th(ch-a)}$	41.6	$^\circ C / W$

**This transistor is an electrostatic sensitive device.
 Please handle with caution.**

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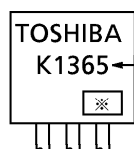
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current		I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$	—	—	± 10	nA
Drain Cut-off Current		I_{DSS}	$V_{DS} = 800V, V_{GS} = 0V$	—	—	300	μA
Drain-Source Breakdown Voltage		$V_{(BR)DSS}$	$I_D = 10mA, V_{GS} = 0V$	1000	—	—	V
Gate Threshold Voltage		V_{th}	$V_{DS} = 10V, I_D = 1mA$	1.5	—	3.5	V
Drain-Source ON Resistance		$R_{DS(ON)}$	$I_D = 4A, V_{GS} = 10V$	—	1.5	1.8	Ω
Forward Transfer Admittance		$ Y_{fs} $	$V_{DS} = 20V, I_D = 4A$	2.0	4.0	—	S
Input Capacitance		C_{iss}	$V_{DS} = 25V, V_{GS} = 0V, f = 1MHz$	—	1300	—	pF
Reverse Transfer Capacitance		C_{rss}		—	100	—	
Output Capacitance		C_{oss}		—	180	—	
Switching Time	Rise Time	t_r		—	25	—	ns
	Turn-on Time	t_{on}		—	40	—	
	Fall Time	t_f		—	20	—	
	Turn-off Time	t_{off}		—	100	—	
Total Gate Charge (Gate-Source Plus Gate-Drain)		Q_g	$V_{DD} \doteq 400V, V_{GS} = 10V, I_D = 7A$	—	120	—	nC
Gate-Source Charge		Q_{gs}		—	70	—	
Gate-Drain ("Miller") Charge		Q_{gd}		—	50	—	

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Continuous Drain Reverse Current	I_{DR}	—	—	—	7	A
Pulse Drain Reverse Current	I_{DRP}	—	—	—	21	A
Diode Forward Voltage	V_{DSF}	$I_{DR} = 7A, V_{GS} = 0V$	—	—	-1.9	V

MARKING



※ Lot Number

□ □ — Month (Starting from Alphabet A)

— Year (Last Number of the Christian Era)

